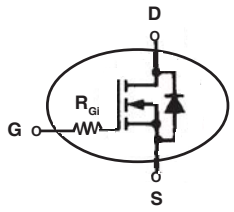
IXYS

LinearL2™ Power MOSFET w/ Extended FBSOA

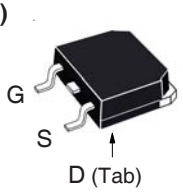
IXTH30N50L2
IXTQ30N50L2
IXTT30N50L2

V_{DSS} = 500V
I_{D25} = 30A
$R_{DS(on)}$ ≤ 215mΩ

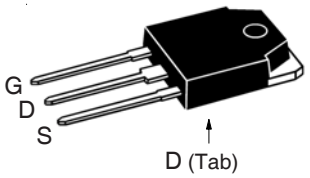
N-Channel Enhancement Mode



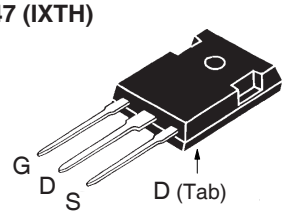
TO-268 (IXTT)



TO-3P (IXTQ)



TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	500	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	T_C = 25°C	30	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	60	A
I_A	T_C = 25°C	30	A
E_{AS}	T_C = 25°C	1.5	J
P_D	T_C = 25°C	400	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-247&TO-3P)	1.13 / 10	Nm/lb.in
Weight	TO-268	4.0	g
	TO-3P	5.5	g
	TO-247	6.0	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	500			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	2.5		4.5	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			50	μA
	T_J = 125°C			300	μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			215	mΩ

Features

- Designed for Linear Operation
- International Standard Packages
- Avalanche Rated
- Guaranteed FBSOA at 75°C

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Solid State Circuit Breakers
- Soft Start Controls
- Linear Amplifiers
- Programmable Loads
- Current Regulators

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	9	12	15	S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		8100		pF
C_{oss}			530		pF
C_{rss}			115		pF
R_{Gi}	Integrated Gate Input Resistor		3.5		Ω
$t_{d(on)}$	**Resistive Switching Times** V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25} R_G = 0Ω (External)		35		ns
t_r			117		ns
$t_{d(off)}$			94		ns
t_f			40		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		240		nC
Q_{gs}			58		nC
Q_{gd}			135		nC
R_{thJC}				0.31	°C/W
R_{thCS}	(TO-247&TO-3P)		0.25		°C/W

Safe Operating Area Specification

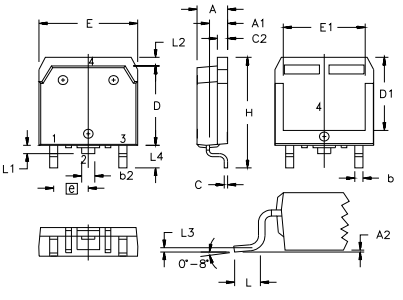
Symbol	Test Conditions	Characteristic Values Min.	Typ.	Max.	
SOA	V_{DS} = 400V, I_D = 0.5A, T_C = 75°C, Tp = 2s	200			W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			30	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			120	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = I_S, -di/dt = 100A/μs, V_R = 100V, V_{GS} = 0V		500		ns

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

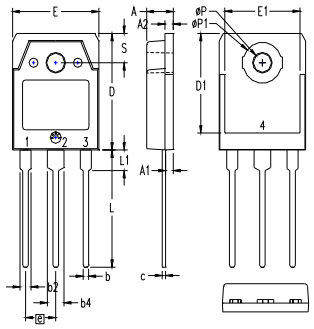
TO-268 Outline



Terminals: 1 - Gate 2,4 - Drain
3 - Source

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

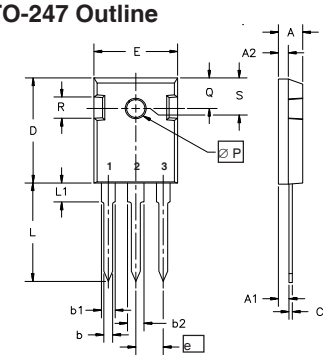
TO-3P Outline



1 – GATE
2 – DRAIN
3 – SOURCE
4 – DRAIN

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
øP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

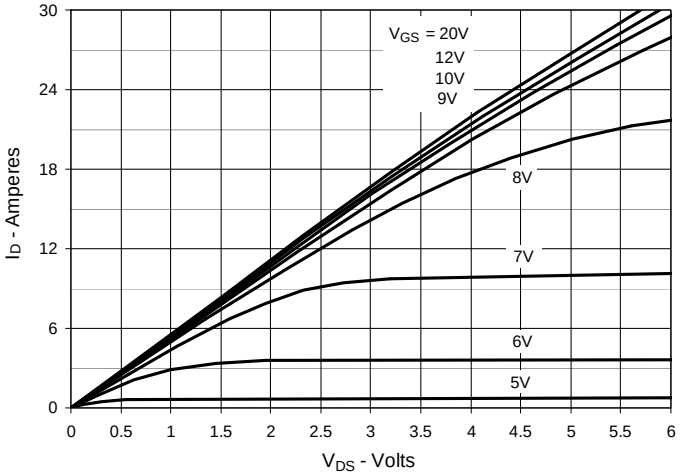


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

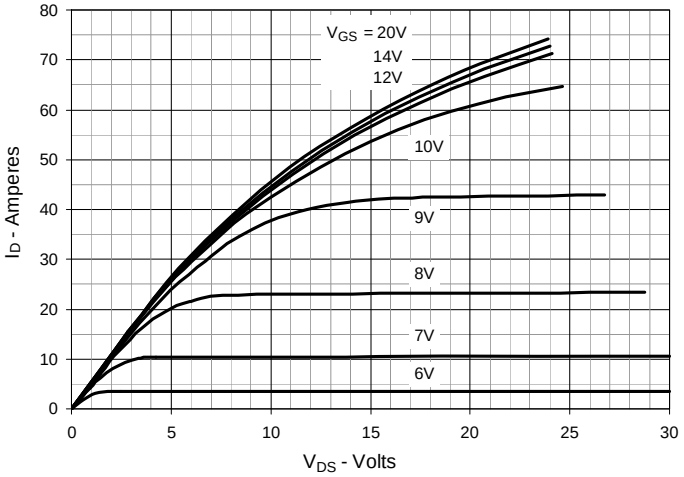


Fig. 3. Output Characteristics @ T_J = 125ºC

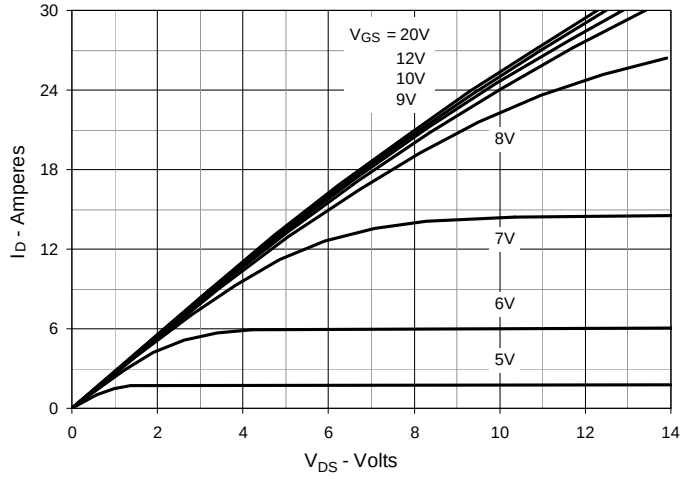


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 15A Value vs. Junction Temperature

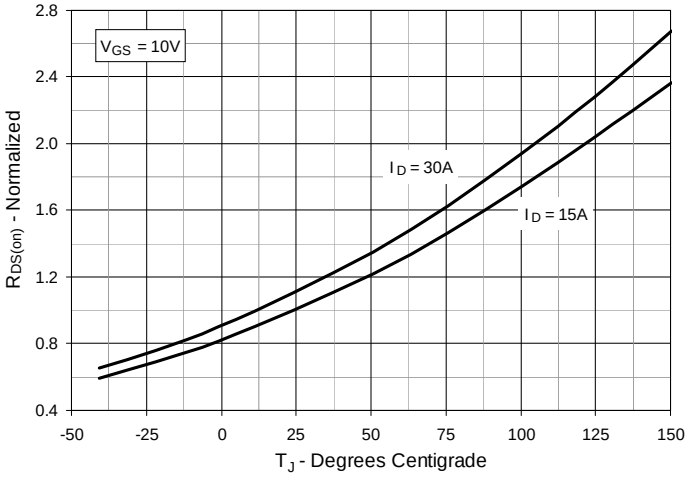


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 15A Value vs. Drain Current

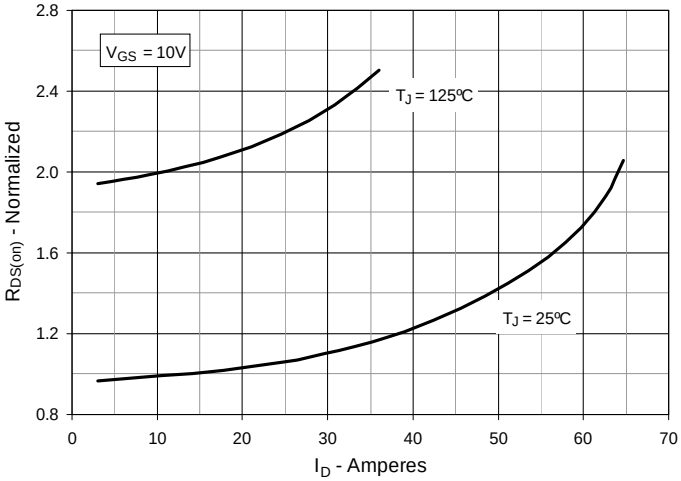
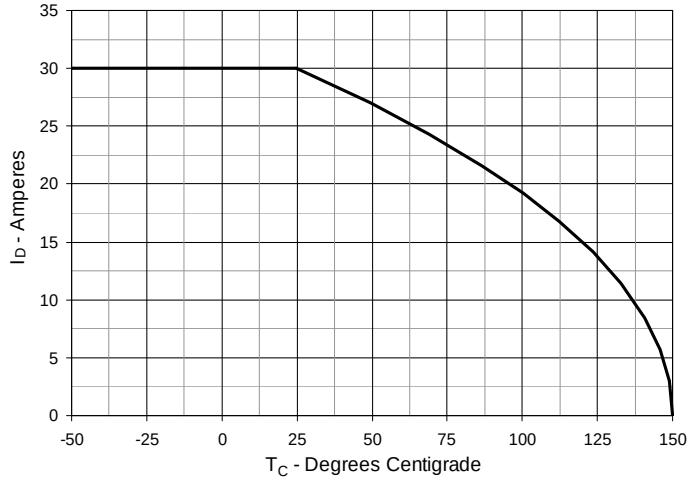


Fig. 6. Maximum Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

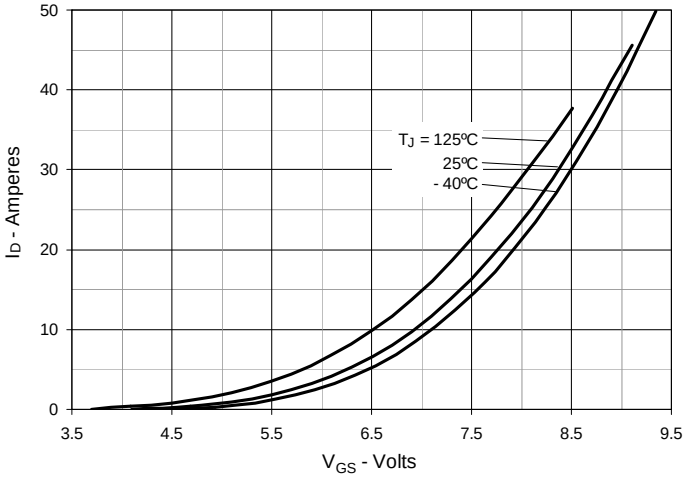


Fig. 8. Transconductance

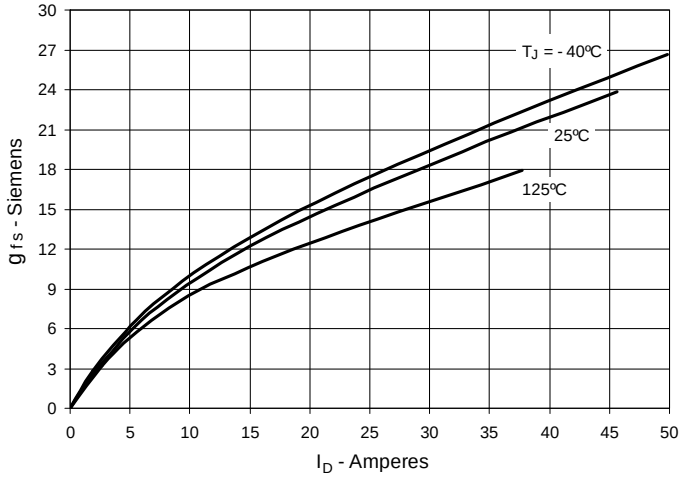


Fig. 9. Forward Voltage Drop of Intrinsic Diode

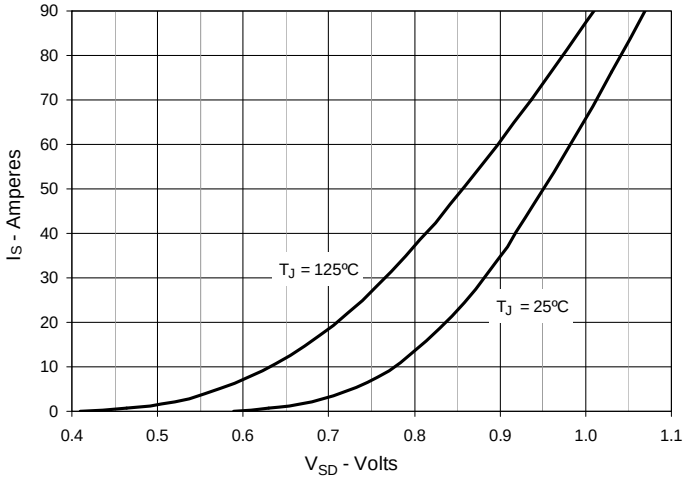


Fig. 10. Gate Charge

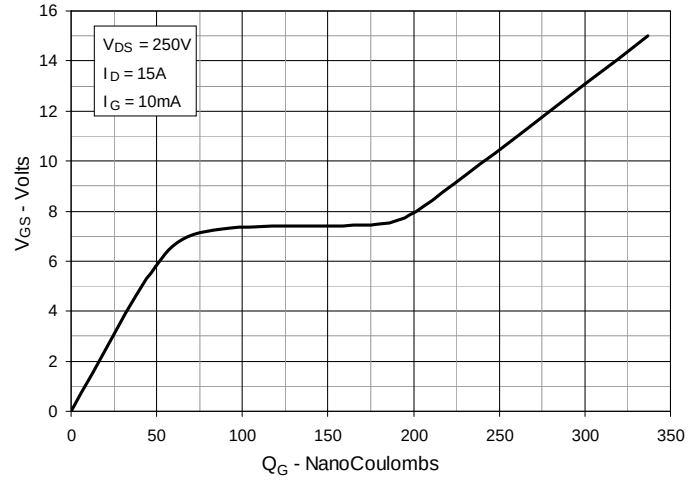


Fig. 11. Capacitance

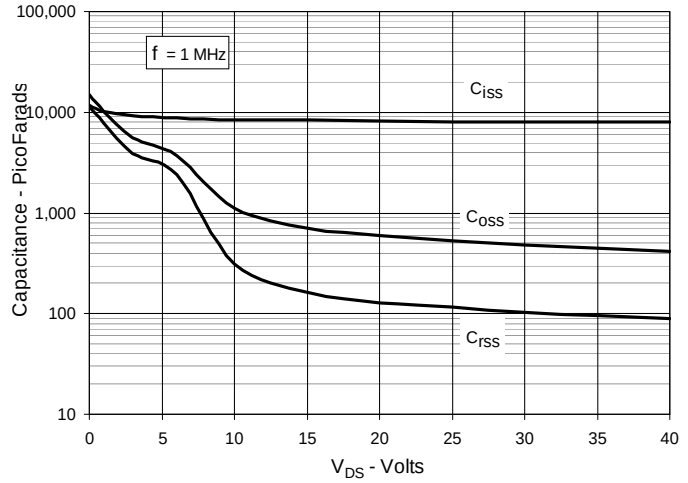
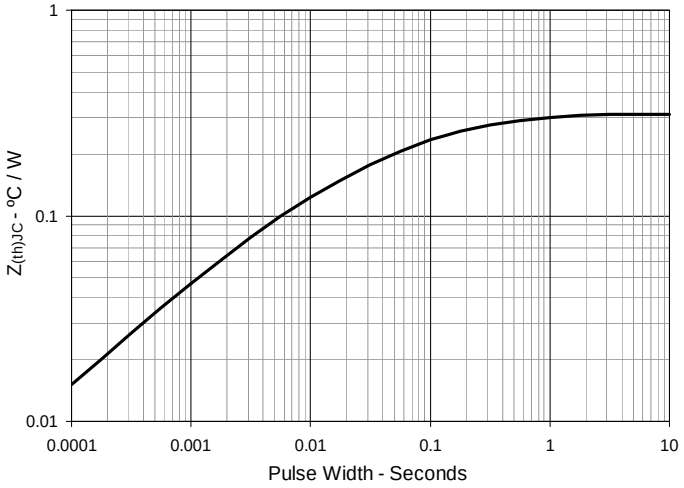


Fig. 12. Maximum Transient Thermal Impedance



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Fig. 13. Forward-Bias Safe Operating Area @ T_C = 25ºC

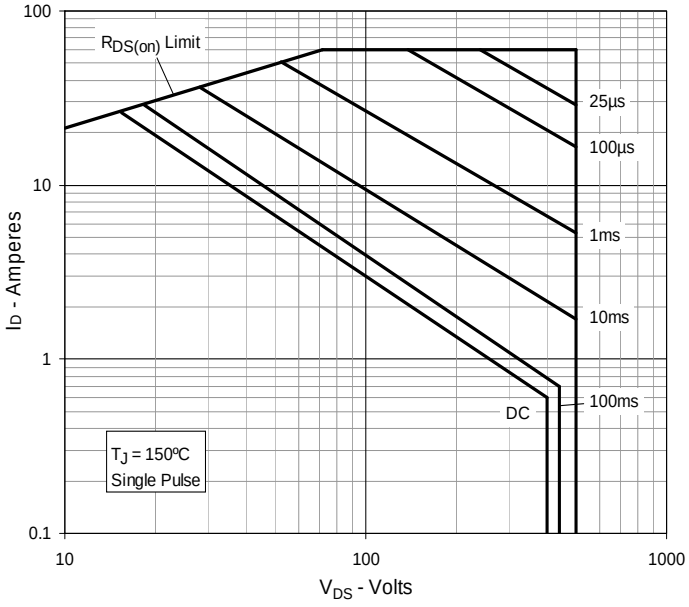
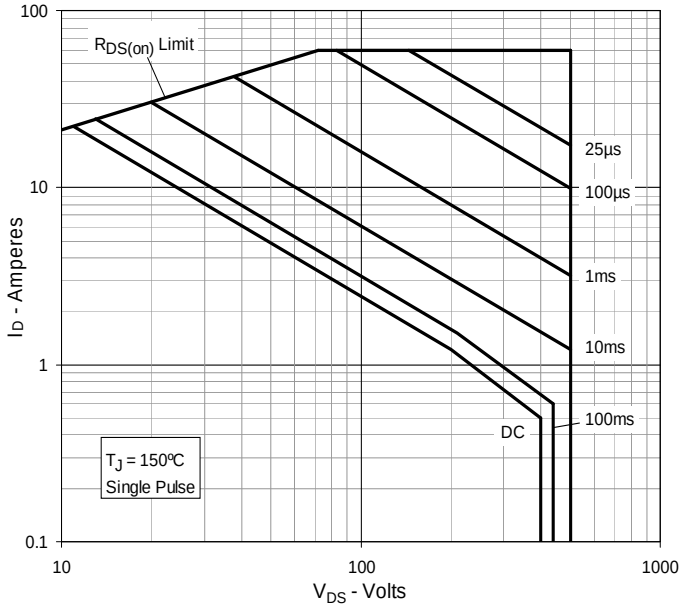


Fig. 14. Forward-Bias Safe Operating Area @ T_C = 75ºC



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